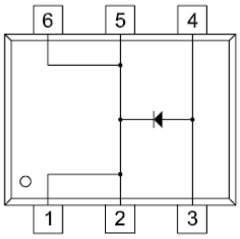
## Silicon Schottky Diode CMLSH05-4

### FEATURES

- Low $V_F$.

Lead-free



**SOT-363**

### APPLICATIONS

- For applications requiring a low forward voltage drop.

### ORDERING INFORMATION

| Type No. | Marking | Package Code |
|---|---|---|
| CMLSH05-4 | C54 | SOT-363 |

### MAXIMUM RATING @ Ta=25℃ unless otherwise specified

| **Symbol** | **Characteristic** | **Value** | **Unit** |
|---|---|---|---|
| $V_{RRM}$ | Repetitive peak reverse voltage | 40 | V |
| $V_{RWM}$ | Working peak reverse voltage | 200 | V |
| $V_R$ | DC Blocking voltage | 200 | V |
| $V_{R(RMS)}$ | RMS Reverse voltage | 141 | V |
| $I_F$ | Forward Continuous current | 500 | mA |
| $I_{FSM}$ | Forward surge current, tp=8ms | 10 | A |
| $I_{FRM}$ | Peak Repetitive Forward Current ,tp≤1ms | 3.5 | A |
| $P_D$ | Power Dissipation | 250 | mW |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient Air | 500 | ℃/W |
| $T_j, T_{stg}$ | Junction and Storage Temperature | -65 to +150 | ℃ |

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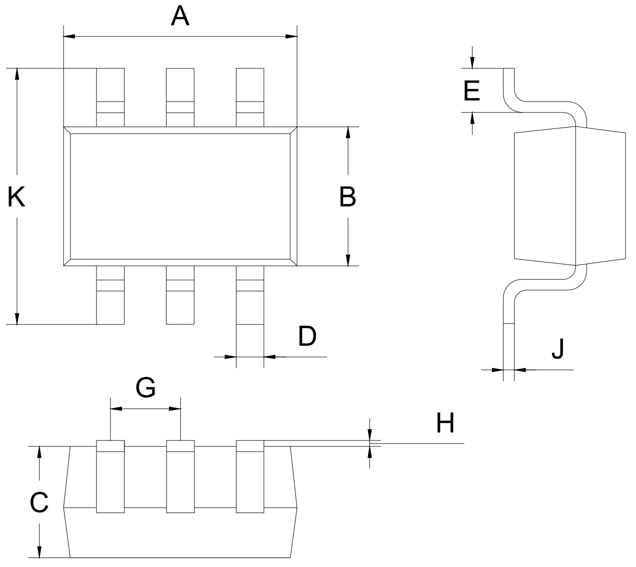
### ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|---|---|---|---|---|---|
| Reverse breakdown voltage | $V_{(BR)R}$ | $I_R$=500μA | 40 | - | V |
| Forward voltage | $V_F$ | $I_F$=100uA<br>$I_F$=1.0mA<br>$I_F$=10mA<br>$I_F$=100mA<br>$I_F$=500mA | -<br>-<br>-<br>-<br>- | 0.13<br>0.21<br>0.27<br>0.35<br>0.47 | V |
| Peak Reverse Current | $I_R$ | $V_R$=10V<br>$V_R$=30V | - | 20<br>100 | uA<br>uA |
| Total Capacitance | $C_T$ | $V_R$=1.0V,f=1.0MHz | - | 50 | pF |

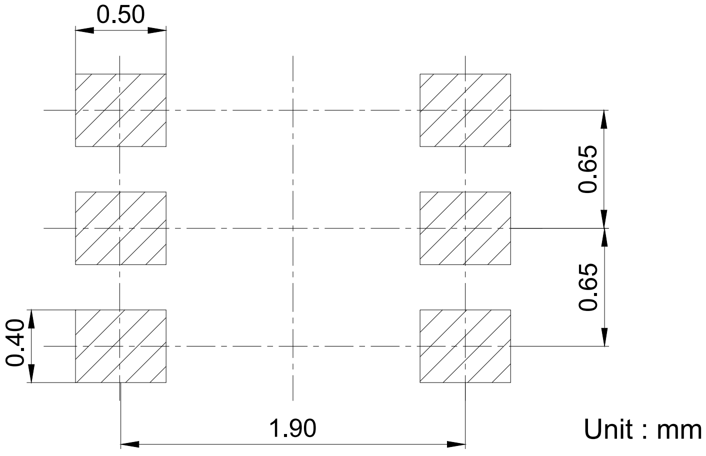
## PACKAGE OUTLINE

Plastic surface mounted package SOT-363



| SOT-363 | | |
|---|---|---|
| Dim | Min | Max |
| A | 2.00 | 2.20 |
| B | 1.15 | 1.35 |
| C | 0.95 Typical | |
| D | 0.25 Typical | |
| E | 0.25 | 0.40 |
| G | 0.60 | 0.70 |
| H | 0.02 | 0.10 |
| J | 0.10 Typical | |
| K | 2.2 | 2.4 |
| All Dimensions in mm | | |

## SOLDERING FOOTPRINT



## PACKAGE INFORMATION

| Device | Package | Shipping |
|---|---|---|
| CMLSH05-4 | SOT-363 | 3000/Tape&Reel |